

Claims

1. (Previously presented) A microelectronic device comprising:
a die, the die comprising a first side, a second side, and an edge;
a first plate, the first plate coupled with the die, the first plate exerting force on the
die to modify the effective coefficient of thermal expansion of the die; and
a package, the die being coupled with the package.
2. (Cancelled)
3. (Previously presented) The microelectronic device of claim 1, where the first
plate modifies the coefficient of thermal expansion of the die to make the
coefficient of thermal expansion of die more closely match the coefficient of
thermal expansion of the package.
4. (Original) The microelectronic device of claim 1, wherein the first plate
comprises a hole, the die fitting within the hole, the edge of the die being coupled
with an edge of the plate by the hole.
5. (Original) The microelectronic device of claim 4, wherein the edge of the die is
soldered with the edge of the first plate.
6. (Original) The microelectronic device of claim 1, wherein a side of the die is
coupled with a side of the first plate.
7. (Original) The microelectronic device of claim 1, further comprising a second
plate coupled with the package.

8. (Original) The microelectronic device of claim 7, wherein the package is attached with the second plate by an adhesive.
9. (Original) The microelectronic device of claim 7, wherein the first plate and second plate are constructed of the same material.
10. (Original) The microelectronic device of claim 9, wherein the first plate and the second plate are constructed of copper.
- 11-30. (Cancelled)
31. (Previously presented) A microelectronic device comprising:
a die, the die comprising a first side, a second side, and an edge;
a first plate, the first plate coupled with the die, the first plate comprising a hole,
the die fitting within the hole, the edge of the die being coupled with an
edge of the plate by the hole, the edge of the die being soldered with the
edge of the first plate; and
a package, the die being coupled with the package.
32. (Previously presented) The microelectronic device of claim 31, wherein the first plate exerts forces on the die to modify its effective coefficient of thermal expansion.
33. (Previously presented) The microelectronic device of claim 32, where the first plate modifies the coefficient of thermal expansion of the die to make the coefficient of thermal expansion of die more closely match the coefficient of thermal expansion of the package.

34. (Previously presented) The microelectronic device of claim 31, further comprising a second plate coupled with the package.
35. (Previously presented) The microelectronic device of claim 34, wherein the package is attached with the second plate by an adhesive.
36. (Previously presented) The microelectronic device of claim 35, wherein the first plate and second plate are constructed of the same material.
37. (Previously presented) The microelectronic device of claim 36, wherein the first plate and the second plate are constructed of copper.